

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC3265

Low Frequency Power Amplifier Applications

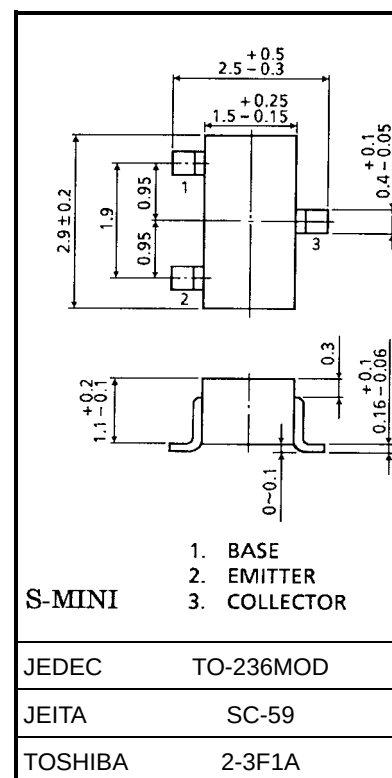
Power Switching Applications

Unit: mm

- High DC current gain: $h_{FE(1)} = 100 \sim 320$
- Low saturation voltage: $V_{CE(sat)} = 0.4 \text{ V (max)}$
($I_C = 500 \text{ mA}$, $I_B = 20 \text{ mA}$)
- Complementary to 2SA1298

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	800	mA
Base current	I_B	160	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$



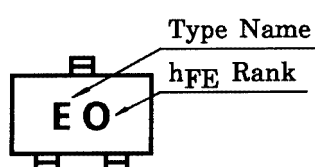
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

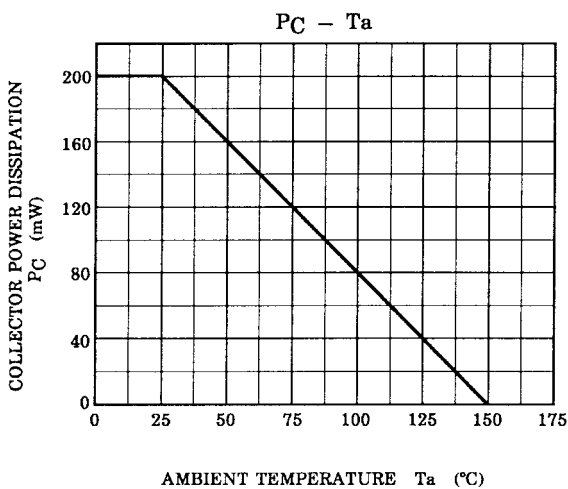
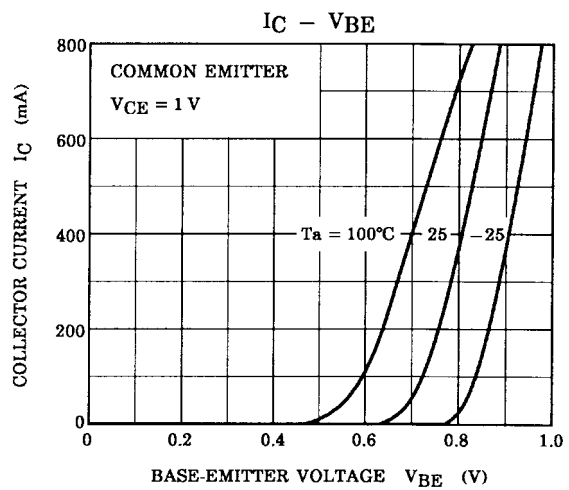
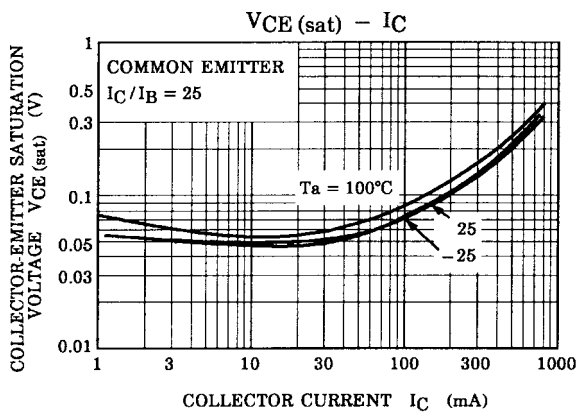
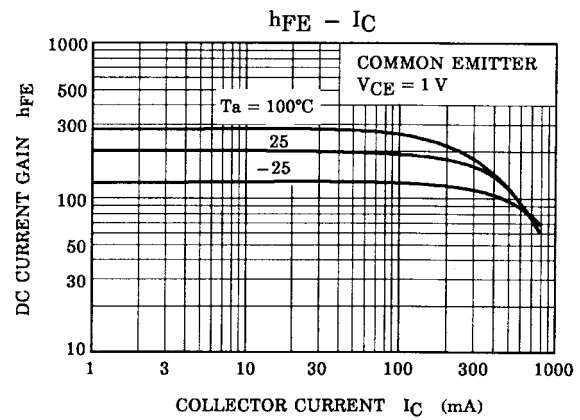
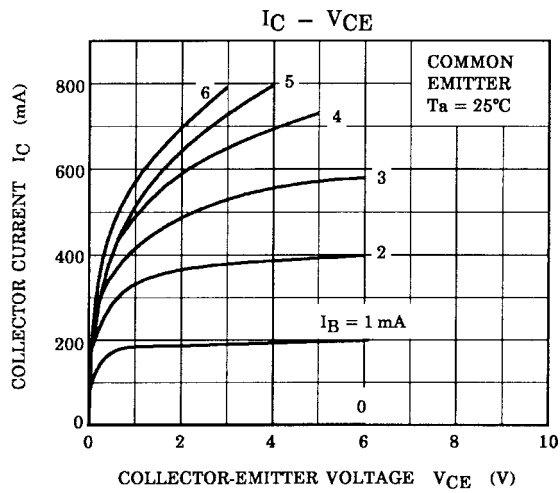
Weight: 0.012 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 30 \text{ V}$, $I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 \text{ V}$, $I_C = 0$	—	—	0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 \text{ mA}$, $I_B = 0$	25	—	—	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1 \text{ mA}$, $I_C = 0$	5	—	—	V
DC current gain	$h_{FE(1)}$ (Note)	$V_{CE} = 1 \text{ V}$, $I_C = 100 \text{ mA}$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = 1 \text{ V}$, $I_C = 800 \text{ mA}$	40	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 \text{ mA}$, $I_B = 20 \text{ mA}$	—	—	0.4	V
Base-emitter voltage	V_{BE}	$V_{CE} = 1 \text{ V}$, $I_C = 10 \text{ mA}$	0.5	—	0.8	V
Transition frequency	f_T	$V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$	—	120	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$	—	13	—	pF

Note: $h_{FE(1)}$ classification O: 100~200, Y: 160~320

Marking





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